

GS3D20120D

Silicon Carbide Schottky Diode

$$V_{RRM} = 1200 \text{ V}$$

$$I_F, T_c < 135^\circ \text{C} = 32 \text{ A}$$

$$Q_c = 132 \text{ nC}$$

Features

- 1.2-KVolt Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Positive Temperature Coefficient on V_F

Benefits

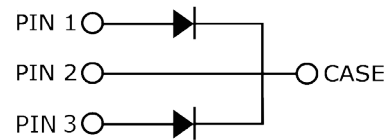
- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switch Mode Power Supplies
- Power Factor Correction
- Motor Drives



Part Number	Package	Marking
GS3D20120D	TO-247-3	GS3D20120D



Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value		Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V		
V_{RSM}	Surge Peak Reverse Voltage	1300	V		
V_{DC}	DC Blocking Voltage	1200	V		
I_F	Continuous Forward Current(Per Leg/Device)	16/32	A	$T_c < 135^\circ\text{C}$, No AC component	
I_{FRM}	Repetitive Peak Forward Surge Current	47* 31.5*	A	$T_c = 25^\circ\text{C}$, $t_p = 10$ ms, Half Sine Pulse $T_c = 110^\circ\text{C}$, $t_p = 10$ ms, Half Sine Pulse	
I_{FSM}	Non-Repetitive Peak Forward Surge Current	71* 59.5*	A	$T_c = 25^\circ\text{C}$, $t_p = 10$ ms, Half Sine Pulse $T_c = 110^\circ\text{C}$, $t_p = 10$ ms, Half Sine Pulse	
P_{tot}	Power Dissipation(Per Leg/Device)	176/352 76/152	W	$T_c = 25^\circ\text{C}$ $T_c = 110^\circ\text{C}$	
T_c	Maximum Case Temperature	135	$^\circ\text{C}$		
T_j	Operating Junction Range	-55 to +175	$^\circ\text{C}$		
T_{stg}	Storage Temperature Range	-55 to +135	$^\circ\text{C}$		
	TO-247 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	

* Per Leg, ** Per Device

Electrical Characteristics (Per Leg)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.5 2.2	1.8 3	V	$I_F = 10\text{ A } T_J = 25^\circ\text{C}$ $I_F = 10\text{ A } T_J = 175^\circ\text{C}$	
I_R	Reverse Current	35 65	200 400	μA	$V_R = 1200\text{ V } T_J = 25^\circ\text{C}$ $V_R = 1200\text{ V } T_J = 175^\circ\text{C}$	
Q_C	Total Capacitive Charge	66		nC	$V_R = 1200\text{ V}, I_F = 10\text{ A}$ $di/dt = 200\text{ A}/\mu\text{s}$ $T_J = 25^\circ\text{C}$	
C	Total Capacitance	754 45 38		pF	$V_R = 0\text{ V}, T_J = 25^\circ\text{C}, f = 1\text{ MHz}$ $V_R = 400\text{ V}, T_J = 25^\circ\text{C}, f = 1\text{ MHz}$ $V_R = 800\text{ V}, T_J = 25^\circ\text{C}, f = 1\text{ MHz}$	

Note:

1. This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.85* 0.43**		$^\circ\text{C}/\text{W}$		

* Per Leg, ** Per Device

Typical Performance (Per Leg)

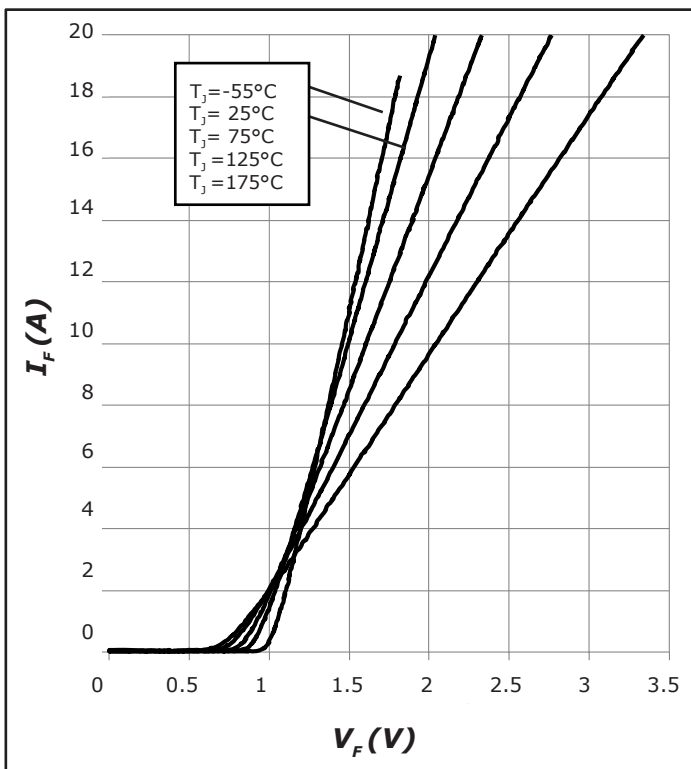


Figure 1. Forward Characteristics

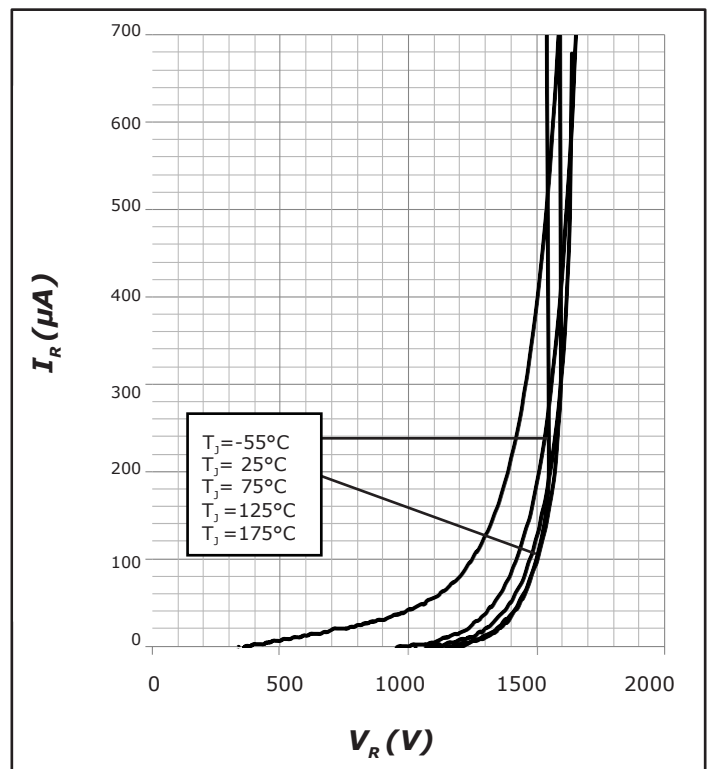


Figure 2. Reverse Characteristics

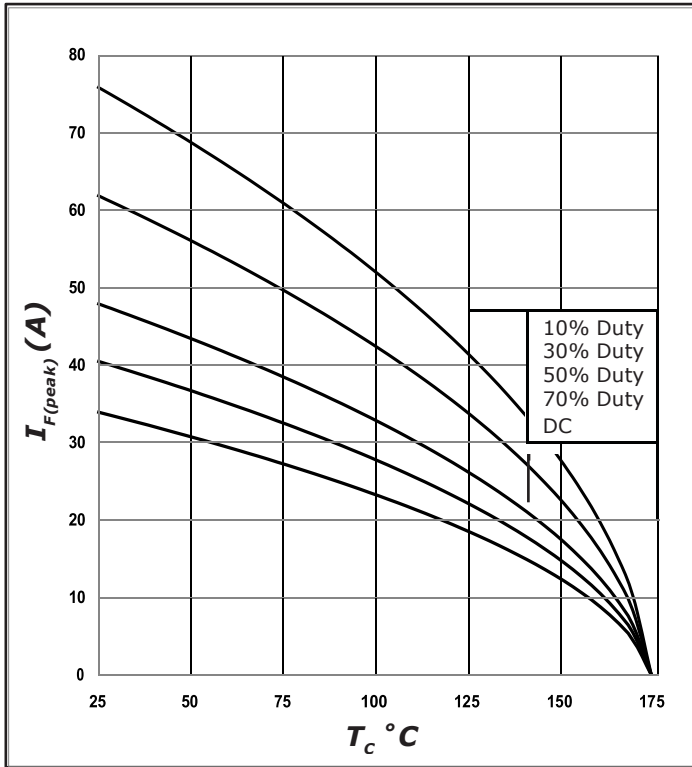


Figure 3. Current Derating

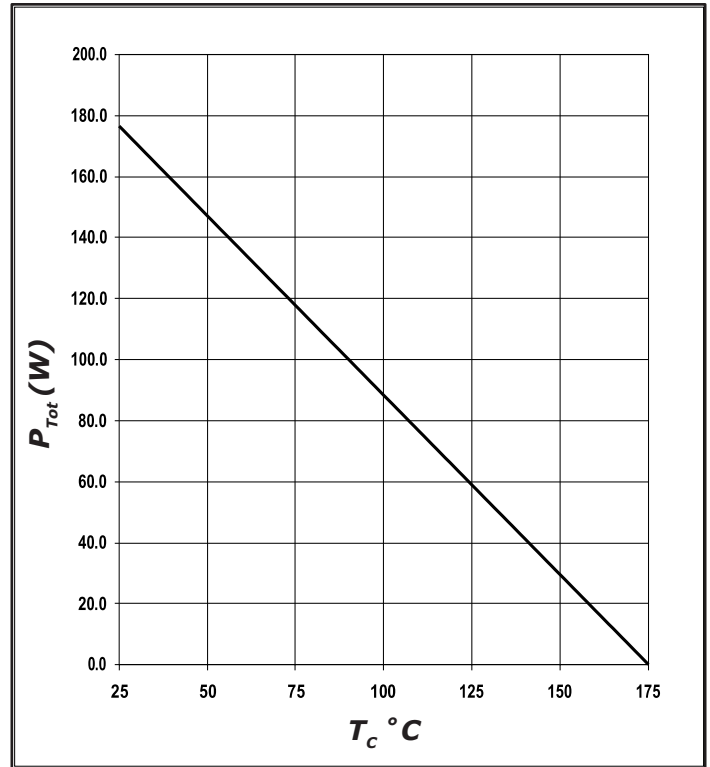


Figure 4. Power Derating

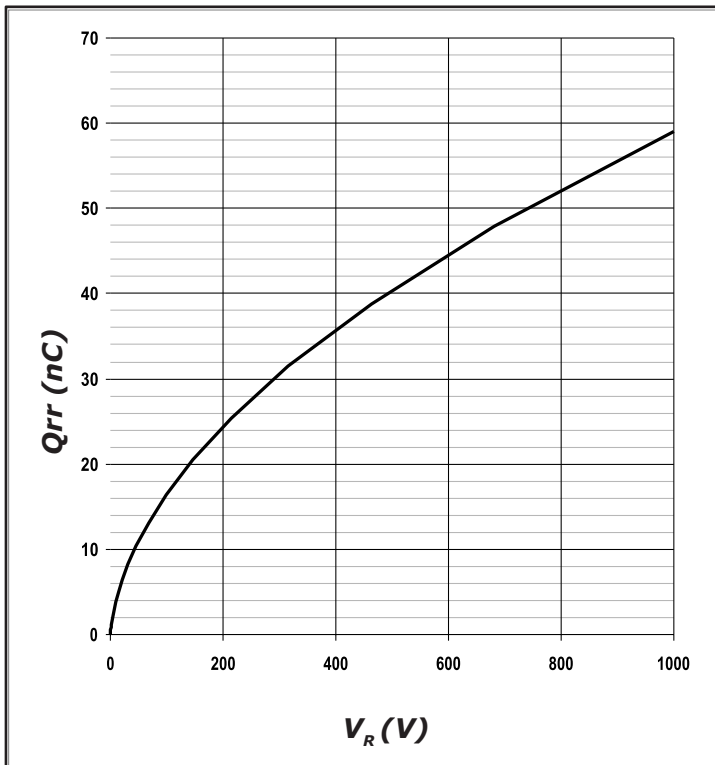


Figure 5. Recovery Charge vs. Reverse Voltage

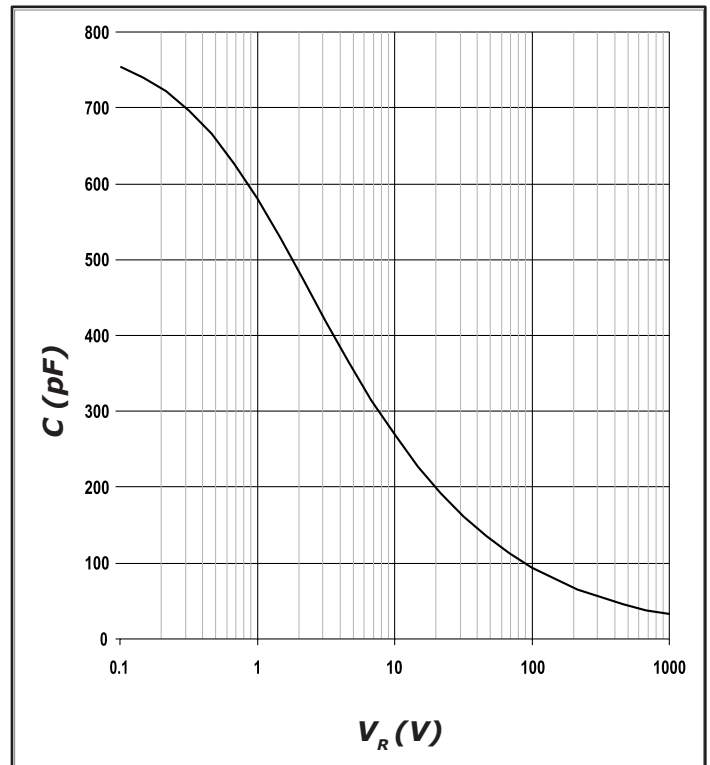


Figure 6. Capacitance vs. Reverse Voltage

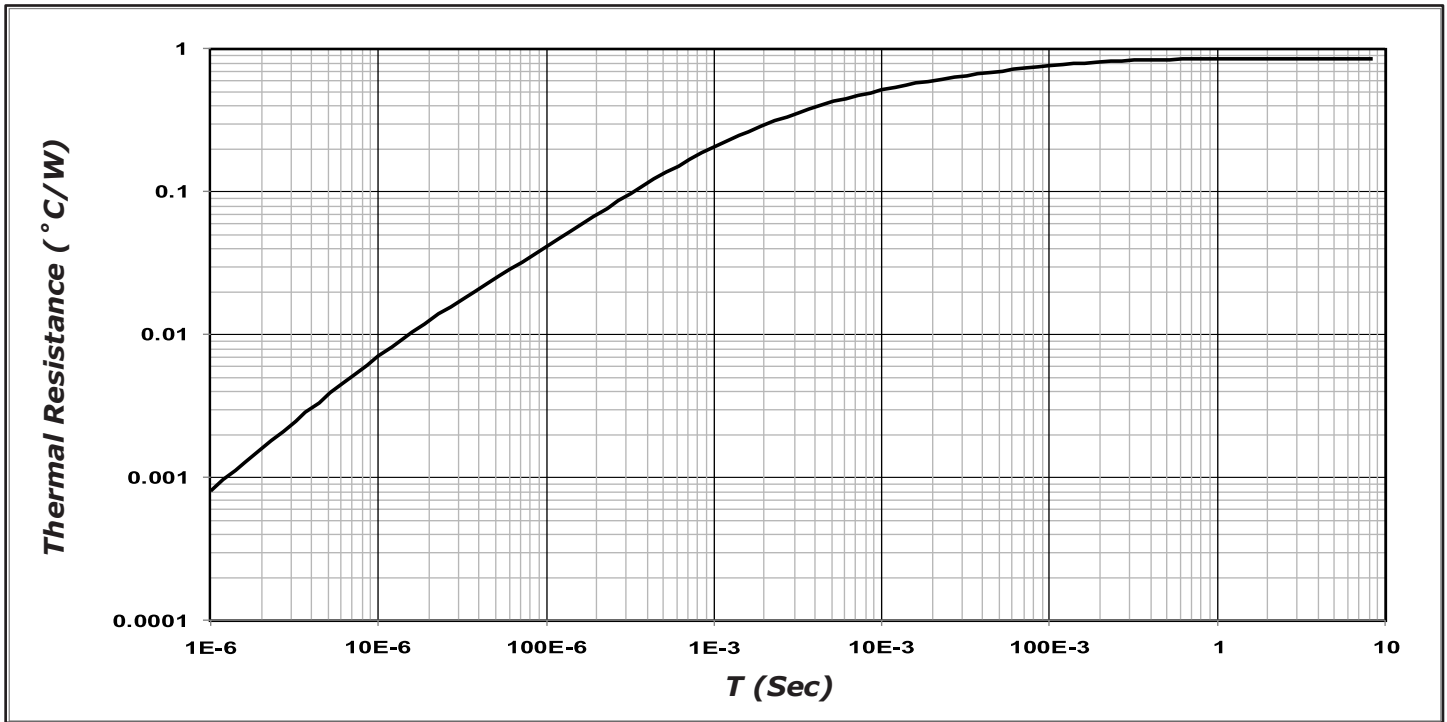
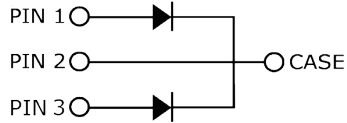
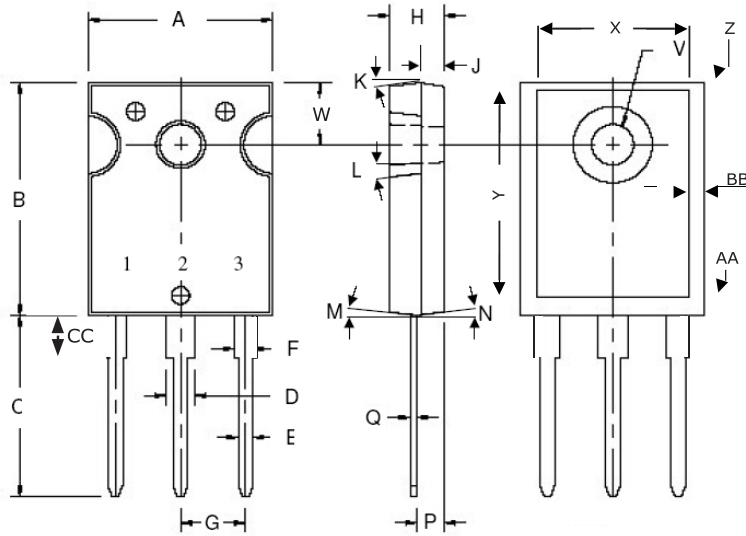


Figure 7. Transient Thermal Impedance

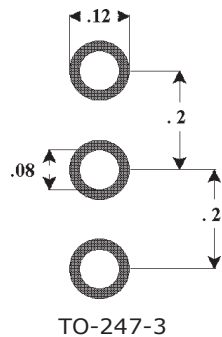
Package Dimensions

Package TO-247-3



POS	Inches		Millimeters	
	Min	Max	Min	Max
A	.605	.635	15.367	16.130
B	.800	.831	20.320	21.10
C	.780	.800	19.810	20.320
D	.095	.133	2.413	3.380
E	.046	.052	1.168	1.321
F	.060	.095	1.524	2.410
G	.215 TYP		5.460 TYP	
H	.175	.205	4.450	5.210
J	.075	.085	1.910	2.160
K	6°	21°	6°	21°
L	4°	6°	4°	6°
M	2°	4°	2°	4°
N	2°	4°	2°	4°
P	.090	.100	2.286	2.540
Q	.020	.030	.508	.762
R	9°	11°	9°	11°
S	9°	11°	9°	11°
T	2°	8°	2°	8°
U	2°	8°	2°	8°
V	.137	.144	3.487	3.658
W	.210	.248	5.334	6.300
X	.502	.557	12.751	14.150
Y	.637	.695	16.180	17.653
Z	.038	.052	0.964	1.321
AA	.110	.140	2.794	3.556
BB	.030	.046	0.766	1.168
CC	.161	.176	4.100	4.472

Recommended Solder Pad Layout



Part Number	Package	Marking
GS3D20120D	TO-247-3	GS3DD20120D